N-Channel 60-V (D-S) 175 °C MOSFET

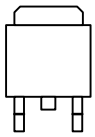
PRODUCT SUMMARY			
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ)
60	0.0039 at V_{GS} = 10 V	110[a]	200

FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- High Threshold Voltage At High Temperature
- 100 % R_g Tested

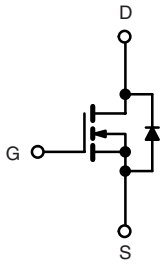
RoHS COMPLIANT

TO-263



Top View

Ordering Information: SUM110N06-3m9H-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	110[a]	A
	T_C = 125 °C		110[a]	
Pulsed Drain Current		I_{DM}	440	
Single Pulse Avalanche Current		I_{AS}	70	
Single Pulse Avalanche Energy	L = 0.1 mH	E_{AS}	245	mJ
Maximum Power Dissipation[b]	T_C = 25 °C	P_D	375[c]	W
	T_A = 25 °C[d]		3.75	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS				
Parameter		**Symbol**	**Limit**	**Unit**
Junction-to-Ambient	PCB Mount[d]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.4	

Notes:
a. Package limited.
b. Duty cycle ≤ 1 %.
c. See SOA curve for voltage derating.
d. When mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min**	**Typ**	**Max**	**Unit**
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 µA	60			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	3.4		4.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			1	µA
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 175 °C			250	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	120			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 30 A		0.00325	0.0039	Ω
		V_{GS} = 10 V, I_D = 30 A, T_J = 125 °C			0.0063	
		V_{GS} = 10 V, I_D = 30 A, T_J = 175 °C			0.0082	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 30 A	30			S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		15 800		pF
Output Capacitance	C_{oss}			1050		
Reverse Transfer Capacitance	C_{rss}			600		
Gate Resistance	R_g	f = 1 MHz	0.6	1.2	1.8	Ω
Total Gate Charge[c]	Q_g	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 110 A		200	300	nC
Gate-Source Charge[c]	Q_{gs}			80		
Gate-Drain Charge[c]	Q_{gd}			45		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 30 V, R_L = 0.27 Ω $I_D \cong$ 110 A, V_{GEN} = 10 V, R_g = 2.5 Ω		45	70	ns
Rise Time[c]	t_r			160	240	
Turn-Off Delay Time[c]	$t_{d(off)}$			75	115	
Fall Time[c]	t_f			14	25	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)[b]						
Continuous Current	I_S				110	A
Pulsed Current	I_{SM}				240	
Forward Voltage[a]	V_{SD}	I_F = 85 A, V_{GS} = 0 V		1.1	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 85 A, di/dt = 100 A/µs		65	100	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			4.4	6.6	A
Reverse Recovery Charge	Q_{rr}			143	330	nC

Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.